

40V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	20mΩ @ V _{GS} = 10V	8.0A
40V	28mΩ @ V _{GS} = 4.5V	6.7A

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
 A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

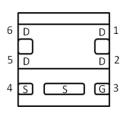
Mechanical Data

- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208[®]
- Weight: 0.0065 grams (Approximate)

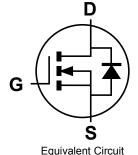
U-DFN2020-6 (Type E)



Bottom View



Pin Out



Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity Per Reel
DMN4020LFDE-7	NE	7	3000
DMN4020LFDE-13	NE	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1:



NE = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2013	 2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	Α	 G	Н	I	J	K	L	M	N	0	Р

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2:



NE = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: H = 2020)

W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	0	1	2	3	4	5	6	7	8

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	Х	Υ	Z



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	40	V	
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Prais Current (Note 6) // = 10//	Steady State	T _A = +25°C T _A = +70°C	I _D	8.0 6.3	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t < 10s	T _A = +25°C T _A = +70°C	I _D	9.5 7.5	А
Continuous Drain Current (Note 6) // - 4 5/	Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$				А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t < 10s	T _A = +25°C T _A = +70°C	I _D	8.0 6.4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%		I _{DM}	32	A	
Maximum Body Diode Continuous Current	I _S	2.5	Α		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Bower Dissipation (Note 5)	T _A = +25°C	Б	0.66	W	
Total Power Dissipation (Note 5)	T _A = +70°C	P_{D}	0.42		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	р	189	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	132	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	В	2.03	W	
Total Fower Dissipation (Note 6)	T _A = +70°C	P_{D}	1.31	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	П	61		
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	43	°C/W	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9.3		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

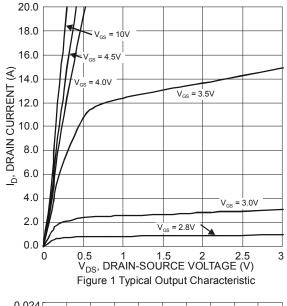
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

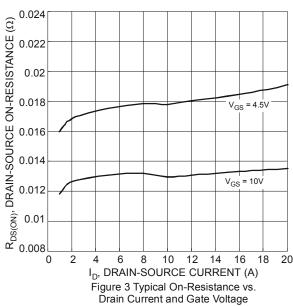
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40		_	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}			1	μΑ	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.4		2.4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Б		15	20	mΩ	$V_{GS} = 10V, I_D = 8A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	20	28	11122	$V_{GS} = 4.5V, I_D = 4A$	
Diode Forward Voltage	V_{SD}	1	0.7	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1060	_	рF	.,	
Output Capacitance	Coss	I	84	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	58	_	рF	1 - 1.000112	
Gate Resistance	R_g	_	1.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	8.8	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	19.1	_	nC	\/ - 20\/ I - 0A	
Gate-Source Charge	Q_{gs}	_	3.0	_	nC	$V_{DS} = 20V, I_D = 8A$	
Gate-Drain Charge	Q_{gd}	_	2.5	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	5.3	_	ns		
Turn-On Rise Time	t _R	_	7.1	_	ns	$V_{DS} = 20V, R_L = 2.5\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	15.1	_	ns	$V_{GS} = 10V, R_G = 3\Omega$	
Turn-Off Fall Time	t _F	_	4.8	_	ns		
Reverse Recovery Time	t _{RR}		10.5	_	ns	1 - 00 di/dt - 1000///c	
Reverse Recovery Charge	Q_{RR}	1	4.15	_	nC	I _F = 8A, di/dt = 100A/μs	

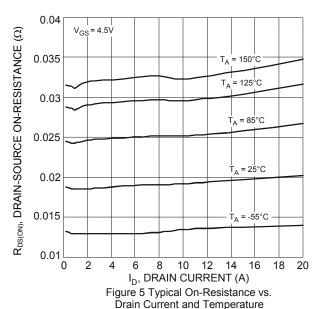
Notes: 5. Device

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

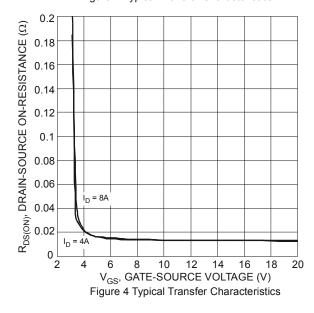


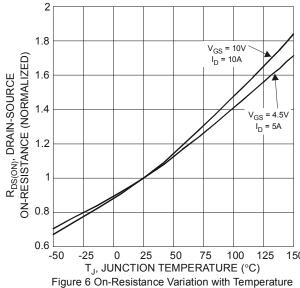




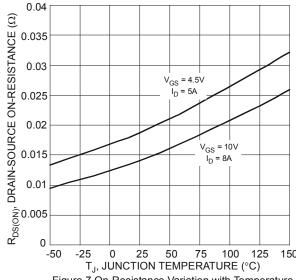


20 V_{DS} = 5.0V 16 ID, DRAIN CURRENT (A) 12 T_A = 150°C = 125°C 4 0 2 2.5 0.5 1.5 3 3.5 4 V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics









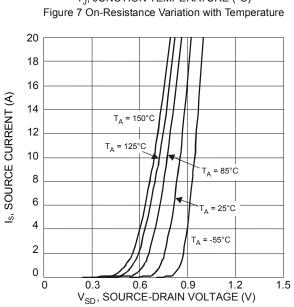
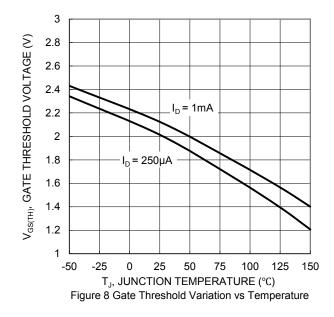
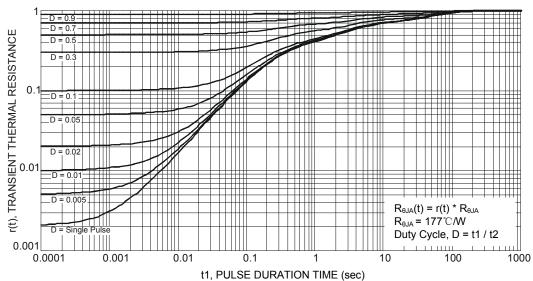


Figure 9 Diode Forward Voltage vs. Current



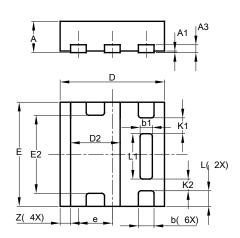




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)

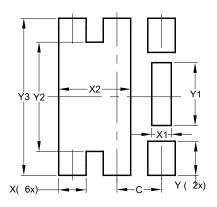


		N2020-	6
		/pe E	
Dim	Min	Max	Тур
Α	0.57	0.63	0.60
A1	0	0.05	0.03
A3	_	-	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
Е	1.95	2.05	2.00
E2	1.40	1.60	1.50
е	_	-	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	_	_	0.305
K2	_	_	0.225
Z	_	_	0.20
All	Dimen	sions i	in mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2 300



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